

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	898	(438/627).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/12 12:03
S1	1	("20020151110").PN.	US-PGPUB; USOCR	OR	OFF	2005/01/10 09:32
S2	1	(tantalum adj nitride) with (ligand adj bond\$5) with (free near5 ((hydrogen or ("H.sub.2")) adj radical))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 09:13
S3	1078	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) and (hole or aperture or via or trench or open\$4) and ((atomic adj layer adj deposit\$6) or ("ALD"))) and (repeat\$8 or times) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/12 12:03
S4	745	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) same (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD"))) and (repeat\$8 or times) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:33
S5	595	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) with (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD"))) and (repeat\$8 or times) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:32
S6	457	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) with (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD"))) and (repeat\$8 or times) and (barrier or (diffus\$6 adj prevent\$6)) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:33

S7	552	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) same (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and (barrier or (diffus\$6 adj prevent\$6)) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:33
S8	752	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) and (hole or aperture or via or trench or open\$4) and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and (barrier or (diffus\$6 adj prevent\$6)) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:33
S9	222	semiconductor and (insulat\$ adj layer) and hole and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and (barrier) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:00
S10	22254	lim.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:58
S11	173	lim.inv. and bio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:04
S12	3	lim.inv. and bi and (atomic adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:05
S13	239	lim.inv. and bi and o	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:05
S14	1	(lim.inv. and bi and o) and (atomic adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:05

S15	738	(438/652).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:56
S16	232	438/652.ccls. and barrier and ((atomic adj layer deposit\$6) or ("ALD"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 09:08
S17	1	("20040115929").PN.	US-PGPUB; USOCR	OR	OFF	2004/10/18 09:02
S18	2172	(438/586).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:11
S19	276	(438/658).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:11
S20	953	(438/653).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:11
S21	1261	(438/643).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:11
S22	652	(438/683).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:11
S23	2089	438/652,653,658,643,683,586. ccls. and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and @ad<"20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 10:12

S24	1876	438/652,653,658,643,683,586. ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and @ad<"20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 08:55
S25	378	(438/652,653,658,643,683,586. ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and @ad<"20031210") and repe\$9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 10:14
S26	3	((("6482733") or ("6391785") or ("6139700"))).PN.	USPAT; USOCR	OR	OFF	2004/10/19 08:13
S27	5	((("6383924") or ("5811868") or ("4751562") or ("5805421") or ("6440637"))).PN.	USPAT; USOCR	OR	OFF	2004/10/20 08:48
S37	2	((("6300679") or ("20040021211"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/10/19 13:51
S38	1	("20040115913").PN.	US-PGPUB; USOCR	OR	OFF	2005/01/10 10:20
S39	1	("20040115913").PN.	US-PGPUB; USOCR	OR	OFF	2005/01/10 10:51
S40	3	((("6482733") or ("6391785") or ("6139700"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/10 10:51
S42	11	((("6482733") or ("6391785") or ("6139700") or ("6524952") or ("20040087136") or ("6416822") or ("6605874") or ("200401377215") or ("5250467") or ("5310695") or ("6340629") or ("6429086"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/10 13:36
S43	13	((("6482733") or ("6391785") or ("6139700") or ("6524952") or ("20040087136") or ("6416822") or ("6605874") or ("200401377215") or ("5250467") or ("5310695") or ("6340629") or ("6429086") or ("20040053491") or ("20030219979"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/10 13:36
S44	0	((atomic adj layer adj deposit\$6) or ("ALD")) with (inject\$6 adj "SiH.sub.4") with (purg\$6 near35 inert) with (inject\$6 adj "WF.sub. 6") with (inject\$6 adj "NH.sub.3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/10 13:40

S45	0	((atomic adj layer adj deposit\$6) or ("ALD")) same (inject\$6 adj "SiH.sub.4") same (purg\$6 near35 inert) same (inject\$6 adj "WF.sub.6") same (inject\$6 adj "NH.sub.3"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 08:58
S46	1	((atomic adj layer adj deposit\$6) or ("ALD")) and (inject\$6 adj "SiH.sub.4") and (purg\$6 near35 inert) and (inject\$6 adj "WF.sub.6") and (inject\$6 adj "NH.sub.3"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/10 13:41
S47	105	438/652,653,658,643,683,586. ccls. and ((tungsten adj silicon adj nitride) or ("WSiN")) and @ad<"20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/08 14:42
S48	0	(438/652,653,658,643,683,586. ccls. with ((tungsten adj silicon adj nitride) or ("WSiN"))) and @ad<"20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 08:57
S49	0	("438"/\$.ccls. with ((tungsten adj silicon adj nitride) or ("WSiN"))) and @ad<"20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 08:57
S50	0	("257"/\$.ccls. with ((tungsten adj silicon adj nitride) or ("WSiN"))) and @ad<"20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 08:58
S51	114	(semiconductor with ((tungsten adj silicon adj nitride) or ("WSiN"))) and @ad<"20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 08:58
S52	1	S51 and (inject\$6 adj ("SiH.sub.4")) and (purg\$6 near35 inert) and (inject\$6 adj ("WF.sub.6")) and (inject\$6 adj ("NH.sub.3"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 09:02
S53	1	S51 and (("SiH.sub.4")) and (purg\$6 near35 inert) and (("WF.sub.6")) and (("NH.sub.3"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 09:02

S54	112	438/652,653,658,643,683,586. ccls. and ((tungsten adj silicon adj nitride) or ("WSiN")) and @ad<"20031210"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/08 14:43
S55	596	"438"/\$.ccls. and ((tungsten adj silicon adj nitride) or ("WSiN")) and @ad<"20031210"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/08 14:42
S56	718	"257"/\$.ccls. and ((tungsten adj silicon adj nitride) or ("WSiN")) and @ad<"20031210"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 07:01
S57	0	(438/652,653,658,643,683,586. ccls. and ((tungsten adj silicon adj nitride) or ("WSiN"))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/08 14:43
S58	0	(438/652,653,658,643,683,586. ccls. and ((tungsten adj silicon adj nitride) or ("WSiN"))).clm.	US-PGPUB	OR	ON	2005/09/08 14:43
S59	18	"257"/\$.ccls. and ((tungsten adj silicon adj nitride) or ("WSiN")) and @ad<"20031210" and inject\$4 and purg\$5 and (tungsten or ("W"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 07:07
S60	15	"438"/\$.ccls. and ((tungsten adj silicon adj nitride) or ("WSiN")) and @ad<"20031210" and inject\$4 and purg\$5 and (tungsten or ("W"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 09:07
S61	4	((("5512771") or ("20010017390"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/09 12:58